

Utilization of GaN:Eu³⁺ for detection of programmed cell death

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Evidence of Singlet-Triplet Crossing in Photoluminescence of Positively Charged Excitons in GaAs Quantum Wells

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Built-in electric field and large Stokes shift in near-lattice-matched GaN/AlInN quantum wells

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Controlling the Aspect Ratio of Quantum Dots: From Columnar Dots to Quantum Rods

L. H. Li, G. Patriarche, N. Chauvin, P. Ridha, M. Rossetti, J. Andrzejewski, G. Sęk, J. Misiewicz, A. Fiore

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Technology and characterisation of GaAsN/GaAs heterostructures for detector applications

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